SGM2358

PRODUCT DESCRIPTION

The SGM2358 has dual rail-to-rail output voltage feedback amplifiers in one package. It takes the minimum operating supply voltage down to 3V and the maximum recommended supply voltage is 5.5 V. SGM2358 is specified over the extended -40°C to +85°C temperature range.

The amplifier in SGM2358 provides 1MHz bandwidth, Very low input bias currents of 10pA, these features enable SGM2358 to be used for integrators, photodiode amplifiers, and piezoelectric sensors. Rail-to-rail output feature is useful for designers to buffer ASIC in single-supply systems.

Applications of SGM2358 include safety monitoring, portable equipment, battery and power supply control, signal conditioning and interfacing for transducers in low power systems.

The SGM2358 comes in SO-8 package.

1MHz, General Purpose CMOS Operational Amplifier

FEATURES

- Low Cost
- Rail-to-Rail Output
 - 1.7mV Typical Vos
- Unity Gain Stable
- Gain Bandwidth Product: 1MHz
- Very Low Input Bias Currents: 10pA
- Input Common-Mode Voltage Range Includes Ground
- Operates from 3 V to 5.5 V
- Small Packaging: SO-8

APPLICATIONS

ASIC Input or Output Amplifier Sensor Interface Piezo Electric Transducer Amplifier Medical Instrumentation Mobile Communication Portable Systems Smoke Detectors Notebook PC PCMCIA cards Battery –Powered equipment DSP interface

PIN CONFIGURATION (Top View)





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ELECTRICAL CHARACTERISTICS : $V_s = +5V$

(At $R_L = 100k\Omega$ connected to Vs/2, and Vout = Vs/2, unless otherwise noted)

		SGM2358				
PARAMETER	CONDITION	ТҮР	MIN/MAX OVER TEMPERATURE			
		+25℃	+25℃	-40℃ to +85℃	UNITS	MIN/MAX
INPUT CHARACTERISTICS						
Input Offset Voltage (V _{os})		1.7	7	7.5	mV	MAX
Input Bias Current (I _B)		10			pА	TYP
Input Offset Current (Ios)		10			pА	TYP
Common-Mode Rejection Ratio(CMRR)	$V_{\rm S}$ = 5V, $V_{\rm CM}$ = $$ - 0.1V to 3.3 V	88	70	65	dB	MIN
Open-Loop Voltage Gain(A _{OL})	R_L = 2K Ω ,Vo = 0.1V to 4.9V	100	85	70	dB	MIN
	R_L =10K Ω ,Vo = 0.035V to 4.965V	110	100	90	dB	MIN
Input Offset Voltage Drift ($\Delta V_{OS} / \Delta_T$)		3.5			µV/℃	TYP
OUTPUT CHARACTERISTICS						
Output Voltage Swing from Rail	R _L = 2KΩ	0.8			V	TYP
	R _L = 10KΩ	0.008			V	TYP
Output Current (I _{OUT})		43	35	30	mA	MIN
POWER SUPPLY						
Operating Voltage Range			3.0	3.0	V	MIN
			5.5	5.5	V	MAX
Power Supply Rejection Ratio (PSRR)	V_{s} = +3 V to + 5.5 V					
	$V_{CM} = (-V_S) + 0.5V$	80	70	65	dB	MIN
Quiescent Current / Amplifier (I_{Ω})	I _{OUT} = 0	0.4	0.95	1	mA	MAX
DYNAMIC PERFORMANCE	C _L = 100pF					
Gain-Bandwidth Product (GBP)		1.0			MHz	TYP
Slew Rate (SR)	G = +1 , 2V Output Step	0.65			V/µs	TYP
Settling Time to 0.1% (t_s)	G = +1, 2 V Output Step	9.0			μs	TYP
Overload Recovery Time	V _{IN} ⋅Gain = Vs	4.0			μs	TYP
Crosstalk	1KHz	-80			dB	TYP
	1MHz	-65			dB	TYP
NOISE PERFORMANCE						
Voltage Noise Density (e _n)	f = 1kHz	42			nV/ \sqrt{Hz}	TYP
	f = 10kHz	38			$nV/_{\sqrt{Hz}}$	TYP

Specifications subject to change without notice.

MODEL	ORDER NUMBER	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	PACKAGE OPTION	MARKING INFORMATION
SGM2358	SGM2358YS/TR	SO-8	-40°C to +85°C	Tape and Reel, 2500	SGM2358YS

PACKAGE/ORDERING INFORMATION

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V+ to V 6.0 V
Storage Temperature Range65°C to +150°C
Junction Temperature
Operating Temperature Range40°C to +85°C
Package Thermal Resistance @ $T_A = 25^{\circ}C$
SO-8, θ _J A125°C/W
Lead Temperature Range (Soldering 10 sec)
260°C
ESD Susceptibility
HBM
MM

NOTES

1. Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION

This integrated circuit can be damaged by ESD. Shengbang Micro-electronics recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

TYPICAL PERFORMANCE CHARACTERISTICS

At $T_A = +25^{\circ}$ C, $V_S = +5V$, and $R_L = 100k\Omega$ connected to Vs/2,unless otherwise noted.



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TYPICAL PERFORMANCE CHARACTERISTICS

At $T_A = +25^{\circ}$ C, $V_S = +5V$, and $R_L = 100k\Omega$ connected to Vs/2,unless otherwise noted.











TYPICAL PERFORMANCE CHARACTERISTICS

At $T_A = +25$ °C, $V_S = +5V$, and $R_L = 100 k\Omega$ connected to Vs/2,unless otherwise noted.



APPLICATION NOTES

Driving Capacitive Loads

The SGM2358 can directly drive 250pF in unity-gain without oscillation. The unity-gain follower (buffer) is the most sensitive configuration to capacitive loading. Direct capacitive loading reduces the phase margin of amplifiers and this results in ringing or even oscillation. Applications that require greater capacitive drive capability should use an isolation resistor between the output and the capacitive load like the circuit in Figure 1. The isolation resistor R_{ISO} and the load capacitor C_L form a zero to increase stability. The bigger the R_{ISO} resistor value, the more stable V_{OUT} will be. Note that this method results in a loss of gain accuracy because R_{ISO} forms a voltage divider with the R_{LOAD}.



Figure 1. Indirectly Driving Heavy Capacitive Load

An improvement circuit is shown in Figure 2, It provides DC accuracy as well as AC stability. R_F provides the DC accuracy by connecting the inverting signal with the output, C_F and R_{Iso} serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving phase margin in the overall feedback loop.



Figure 2. Indirectly Driving Heavy Capacitive Load with DC Accuracy

For no-buffer configuration, there are two others ways to increase the phase margin: (a) by increasing the amplifier's gain or (b) by placing a capacitor in parallel with the feedback resistor to counteract the parasitic capacitance associated with inverting node.

Power-Supply Bypassing and Layout

The SGM2358 operates from either a single +3V to +5.5V supply or dual ±1.5V to ±2.75V supplies. For single-supply operation, bypass the power supply V_{DD} with a 0.1µF ceramic capacitor which should be placed close to the V_{DD} pin. For dual-supply operation, both the V_{DD} and the V_{SS} supplies should be bypassed to ground with separate 0.1µF ceramic capacitors. 2.2µF tantalum capacitor can be added for better performance.



Figure 3. Amplifier with Bypass Capacitors

Typical Application Circuits

Differential Amplifier

The circuit shown in Figure 4 performs the difference function. If the resistors ratios are equal (R4 / R3 = R2 / R1), then V_{OUT} = (Vp - Vn) × R₂ / R₁ + Vref.





Figure 6. Low Pass Active Filter

Figure 4. Differential Amplifier

Instrumentation Amplifier

The circuit in Figure 5 performs the same function as that in Figure 4 but with the high input impedance.



Figure 5. Instrumentation Amplifier

Low Pass Active Filter

The low pass filter shown in Figure 6 has a DC gain of (- R_2/R_1) and the –3dB corner frequency is $1/2\pi R_2 C$. Make sure the filter is within the bandwidth of the amplifier. The Large values of feedback resistors can couple with parasitic capacitance and cause undesired effects such as ringing or oscillation in high-speed amplifiers. Keep resistors value as low as possible and consistent with output loading consideration.

PACKAGE OUTLINE DIMENSIONS

SO-8



REVISION HISTORY

Location

09/07— Data Sheet REV. A	
10/07— Data Sheet changed from REV.A to REV.B	
Changes to ELECTRICAL CHARACTERISTICS about Noise	-

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